

Akira Uedono

List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

375
papers

5,869
citations

35
h-index

57
g-index

422
ext. papers

6,437
ext. citations

2.4
avg, IF

5.38
L-index

#	Paper	IF	Citations
375	Impurity diffusion in ion implanted AlN layers on sapphire substrates by thermal annealing. <i>Japanese Journal of Applied Physics</i> , 2022 , 61, 026501	1.4	0
374	Structure-Property Relationships of Polysilsesquioxanes for Thermal Insulation Materials. <i>ACS Applied Polymer Materials</i> , 2022 , 4, 2851-2859	4.3	3
373	Organic-Inorganic Hybrid Thermal Insulation Materials Prepared via Hydrosilylation of Polysilsesquioxane Having Hydrosilyl Groups and Triallylisocyanurate. <i>ACS Applied Polymer Materials</i> , 2022 , 4, 3726-3733	4.3	3
372	Improved minority carrier lifetime in p-type GaN segments prepared by vacancy-guided redistribution of Mg. <i>Applied Physics Letters</i> , 2021 , 119, 182106	3.4	5
371	Dopant activation process in Mg-implanted GaN studied by monoenergetic positron beam. <i>Scientific Reports</i> , 2021 , 11, 20660	4.9	4
370	Low-temperature annealing behavior of defects in Mg-ion-implanted GaN studied using MOS diodes and monoenergetic positron beam. <i>Japanese Journal of Applied Physics</i> , 2021 , 60, 016502	1.4	5
369	Thermal Insulating Property of Silsesquioxane Hybrid Film Induced by Intramolecular Void Spaces. <i>ACS Applied Polymer Materials</i> , 2021 , 3, 3383-3391	4.3	5
368	Interfacial Conductivity Enhancement and Pore Confinement Conductivity-Lowering Behavior inside the Nanopores of Solid Silica-gel Nanocomposite Electrolytes. <i>ACS Applied Materials & Interfaces</i> , 2021 , 13, 40543-40551	9.5	3
367	Reduced nonradiative recombination rates in c-plane Al _{0.83} In _{0.17} N films grown on a nearly lattice-matched GaN substrate by metalorganic vapor phase epitaxy. <i>Applied Physics Letters</i> , 2021 , 119, 091105	3.4	1
366	Effect of Ag doping on crystallinity and microstrain of LaMnO ₃ nanoparticles: Confirmations of defect levels with positron lifetime and Doppler-broadening calculations. <i>Physica B: Condensed Matter</i> , 2021 , 615, 413087	2.8	4
365	Vacancy-type defects in bulk GaN grown by oxide vapor phase epitaxy probed using positron annihilation. <i>Journal of Crystal Growth</i> , 2021 , 570, 126219	1.6	2
364	Optical and electrical properties of silicon-implanted Al ₂ O ₃ . <i>Japanese Journal of Applied Physics</i> , 2021 , 60, 106502	1.4	0
363	Growth of Al _x Ga _{1-x} N/In _y Ga _{1-y} N hetero structure on AlN/sapphire templates exhibiting Shubnikov-de Haas oscillation. <i>Journal of Crystal Growth</i> , 2021 , 574, 126324	1.6	
362	Hole capture-coefficient of intrinsic nonradiative recombination centers that commonly exist in bulk, epitaxial, and proton-irradiated ZnO. <i>Journal of Applied Physics</i> , 2020 , 127, 215704	2.5	2
361	The Influence of AlN Nucleation Layer on Radio Frequency Transmission Loss of AlN-on-Si Heterostructure. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2020 , 217, 1900755	1.6	3
360	Voids and vacancy-type defects in SiO ₂ /GaN structures probed by monoenergetic positron beams. <i>Journal of Applied Physics</i> , 2020 , 127, 054503	2.5	1
359	Effect of Free-Volume Hole Fraction on Dynamic Mechanical Properties of Epoxy Resins Investigated by Pressure-Volume-Temperature Technique. <i>Journal of Physical Chemistry B</i> , 2020 , 124, 1824-1832	3.4	1

358	Effect of free-volume holes on static mechanical properties of epoxy resins studied by positron annihilation and PVT experiments. <i>Polymer</i> , 2020 , 190, 122225	3.9	7
357	Magnetic properties of metastable bcc phase in Fe ₆₄ Ni ₃₆ alloy synthesized through polyol process. <i>Applied Physics A: Materials Science and Processing</i> , 2020 , 126, 1	2.6	7
356	Origin and dynamic properties of major intrinsic nonradiative recombination centers in wide bandgap nitride semiconductors 2020 ,		2
355	Annealing Behaviours of Open Spaces in Thin Al ₂ O ₃ Films Deposited on Semiconductors Studied Using Monoenergetic Positron Beams. <i>Acta Physica Polonica A</i> , 2020 , 137, 227-230	0.6	
354	Calculation of Positron States and Annihilation Parameters in Gamma and Amorphous Al ₂ O ₃ . <i>Acta Physica Polonica A</i> , 2020 , 137, 231-234	0.6	
353	Free Volume in Epoxy Resins for CFRP Studied by Means of Positron Annihilation. <i>Journal of the Japan Society for Precision Engineering</i> , 2020 , 86, 206-209	0.1	
352	Growth of high-quality GaN by halogen-free vapor phase epitaxy. <i>Applied Physics Express</i> , 2020 , 13, 085509	0.9	2
351	Pore structure analysis of ionic liquid-templated porous silica using positron annihilation lifetime spectroscopy. <i>Microporous and Mesoporous Materials</i> , 2020 , 295, 109964	5.3	2
350	Preparation and characterization of cellulose acetate membranes with TEMPO-oxidized cellulose nanofibrils containing alkyl ammonium carboxylates. <i>Cellulose</i> , 2020 , 27, 1357-1365	5.5	5
349	Morphological characterization and mechanical behavior by dicing and thinning on direct bonded Si wafer. <i>Journal of Manufacturing Processes</i> , 2020 , 58, 811-818	5	4
348	Dynamic Observation and Theoretical Analysis of Initial O ₂ Molecule Adsorption on Polar and m-Plane Surfaces of GaN. <i>Journal of Physical Chemistry C</i> , 2020 , 124, 25282-25290	3.8	4
347	Effects of ultra-high-pressure annealing on characteristics of vacancies in Mg-implanted GaN studied using a monoenergetic positron beam. <i>Scientific Reports</i> , 2020 , 10, 17349	4.9	9
346	Selective trapping of positrons by Ag nanolayers in a V/Ag multilayer system. <i>AIP Advances</i> , 2020 , 10, 035012	1.5	2
345	Annealing behaviors of vacancy-type defects in AlN deposited by radio-frequency sputtering and metalorganic vapor phase epitaxy studied using monoenergetic positron beams. <i>Journal of Applied Physics</i> , 2020 , 128, 085704	2.5	10
344	Investigation of Al ₂ O ₃ /GaN interface properties by sub-bandgap photo-assisted capacitance-voltage technique. <i>AIP Advances</i> , 2019 , 9, 085319	1.5	10
343	Impact of defects on the electrical properties of p-n diodes formed by implanting Mg and H ions into N-polar GaN. <i>Journal of Applied Physics</i> , 2019 , 126, 125102	2.5	7
342	Characterization of the distribution of defects introduced by plasma exposure in Si substrate. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2019 , 37, 011304	2.9	9
341	Structural disorder and in-gap states of Mg-implanted GaN films evaluated by photothermal deflection spectroscopy. <i>Journal of Crystal Growth</i> , 2019 , 511, 15-18	1.6	7

340	Two-dimensional mapping of hydrogen and other elements in materials with microbeam-based transmission ERDA and PIXE. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2019 , 450, 319-322	1.2	2
339	Annealing Behavior of Vacancy-Type Defects in Mg- and H-Implanted GaN Studied Using Monoenergetic Positron Beams. <i>Physica Status Solidi (B): Basic Research</i> , 2019 , 256, 1900104	1.3	15
338	Free volumes introduced by fractures of CFRP probed using positron annihilation. <i>Composites Part A: Applied Science and Manufacturing</i> , 2019 , 122, 54-58	8.4	7
337	Vacancy-type defects in GaN self-assembled nanowires probed using monoenergetic positron beam. <i>Journal of Applied Physics</i> , 2019 , 125, 175705	2.5	1
336	Simple way of finding Ba to Si deposition rate ratios for high photoresponsivity in BaSi ₂ films by Raman spectroscopy. <i>Applied Physics Express</i> , 2019 , 12, 055506	2.4	24
335	Effect of dopant concentration and annealing of Yttrium doped CuO nanocrystallites studied by positron annihilation spectroscopy. <i>Journal of Alloys and Compounds</i> , 2019 , 788, 549-558	5.7	6
334	Room temperature photoluminescence lifetime for the near-band-edge emission of epitaxial and ion-implanted GaN on GaN structures. <i>Japanese Journal of Applied Physics</i> , 2019 , 58, SC0802	1.4	14
333	Er ³⁺ induced point defects in ZnO and impact of Li ⁺ /Na ⁺ /K ⁺ on the vacancy defects in ZnO:Er studied by positron annihilation spectroscopy. <i>Applied Physics A: Materials Science and Processing</i> , 2019 , 125, 1	2.6	5
332	Computational study of positron annihilation parameters for cation mono-vacancies and vacancy complexes in nitride semiconductor alloys. <i>Journal of Physics Condensed Matter</i> , 2019 , 31, 475401	1.8	9
331	In-plane optical polarization and dynamic properties of the near-band-edge emission of an m-plane freestanding AlN substrate and a homoepitaxial film. <i>Applied Physics Letters</i> , 2019 , 115, 151903	3.4	3
330	Valence band edge tail states and band gap defect levels of GaN bulk and In _x Ga _{1-x} N films detected by hard X-ray photoemission and photothermal deflection spectroscopy. <i>Applied Physics Express</i> , 2018 , 11, 021002	2.4	13
329	Ion energy control and its applicability to plasma enhanced atomic layer deposition for synthesizing titanium dioxide films. <i>Thin Solid Films</i> , 2018 , 660, 865-870	2.2	6
328	Vacancy-type defects in Al ₂ O ₃ /GaN structure probed by monoenergetic positron beams. <i>Journal of Applied Physics</i> , 2018 , 123, 155302	2.5	13
327	Effect of ion energies on the film properties of titanium dioxides synthesized via plasma enhanced atomic layer deposition. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2018 , 36, 021515	2.9	8
326	Carrier Trapping by Vacancy-Type Defects in Mg-Implanted GaN Studied Using Monoenergetic Positron Beams. <i>Physica Status Solidi (B): Basic Research</i> , 2018 , 255, 1700521	1.3	39
325	AlN metal-semiconductor field-effect transistors using Si-ion implantation. <i>Japanese Journal of Applied Physics</i> , 2018 , 57, 04FR11	1.4	30
324	The origins and properties of intrinsic nonradiative recombination centers in wide bandgap GaN and AlGaN. <i>Journal of Applied Physics</i> , 2018 , 123, 161413	2.5	70
323	Polarity-dependence of the defect formation in c-axis oriented ZnO by the irradiation of an 8 MeV proton beam. <i>Journal of Applied Physics</i> , 2018 , 123, 161562	2.5	5

322	Positron Annihilation Studies on Chemically Synthesized FeCo Alloy. <i>Scientific Reports</i> , 2018 , 8, 9764	4.9	7
321	Synthesis and characterization of titanium silicon oxide thin films prepared by plasma enhanced atomic layer deposition. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2018 , 36, 06A104	2.9	2
320	Room-temperature photoluminescence lifetime for the near-band-edge emission of (000 1 $\bar{1}$) p-type GaN fabricated by sequential ion-implantation of Mg and H. <i>Applied Physics Letters</i> , 2018 , 113, 191901	3.4	26
319	Annealing behavior of open spaces in ALON films studied by monoenergetic positron beams. <i>Applied Physics Letters</i> , 2018 , 112, 182103	3.4	5
318	Large electron capture-cross-section of the major nonradiative recombination centers in Mg-doped GaN epilayers grown on a GaN substrate. <i>Applied Physics Letters</i> , 2018 , 112, 211901	3.4	35
317	Behavior of copper contamination on backside damage for ultra-thin silicon three dimensional stacking structure. <i>Microelectronic Engineering</i> , 2017 , 167, 23-31	2.5	10
316	Effect of Free-Volume Holes on Dynamic Mechanical Properties of Epoxy Resins for Carbon-Fiber-Reinforced Polymers. <i>Macromolecules</i> , 2017 , 50, 3933-3942	5.5	29
315	Prediction of positron-annihilation parameters for vacancy-type defects in ternary alloy semiconductors by data-scientific approach. <i>Journal of Physics: Conference Series</i> , 2017 , 791, 012023	0.3	1
314	Nitrogen vacancies as a common element of the green luminescence and nonradiative recombination centers in Mg-implanted GaN layers formed on a GaN substrate. <i>Applied Physics Express</i> , 2017 , 10, 061002	2.4	49
313	Development of a microbeam PIXE system for additive light elements in structural materials. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2017 , 404, 92-95	1.2	1
312	Influence of Si wafer thinning processes on (sub)surface defects. <i>Applied Surface Science</i> , 2017 , 404, 82-87	8.7	18
311	Effect of La doping on the lattice defects and photoluminescence properties of CuO. <i>Journal of Alloys and Compounds</i> , 2017 , 709, 496-504	5.7	42
310	Synthesis, defect characterization and photocatalytic degradation efficiency of Tb doped CuO nanoparticles. <i>Advanced Powder Technology</i> , 2017 , 28, 3026-3038	4.6	37
309	Carrier activation in Mg implanted GaN by short wavelength Nd:YAG laser thermal annealing. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2017 , 214, 1700225	1.6	11
308	Electron capture by vacancy-type defects in carbon-doped GaN studied using monoenergetic positron beams. <i>Thin Solid Films</i> , 2017 , 639, 78-83	2.2	10
307	Vacancy-type defects in bulk GaN grown by the Na-flux method probed using positron annihilation. <i>Journal of Crystal Growth</i> , 2017 , 475, 261-265	1.6	10
306	Defect-Resistant Radiative Performance of m-Plane Immiscible Al In N Epitaxial Nanostructures for Deep-Ultraviolet and Visible Polarized Light Emitters. <i>Advanced Materials</i> , 2017 , 29, 1603644	24	30
305	Vacancy-Type Defects in GaN for Power Devices Probed by Positron Annihilation. <i>Defect and Diffusion Forum</i> , 2017 , 373, 183-188	0.7	

304	Surface sealing using self-assembled monolayers and its effect on metal diffusion in porous low- k dielectrics studied using monoenergetic positron beams. <i>Applied Surface Science</i> , 2016 , 368, 272-276	6.7	15
303	Vacancies and electron trapping centers in acidic ammonothermal GaN probed by a monoenergetic positron beam. <i>Journal of Crystal Growth</i> , 2016 , 448, 117-121	1.6	17
302	Nanopores formation and shape evolution in Ge during intense ionizing irradiation. <i>Microporous and Mesoporous Materials</i> , 2016 , 225, 323-330	5.3	6
301	Impacts of Dislocations and Point Defects on the Internal Quantum Efficiency of the Near-Band-Edge Emission in AlGa _N -Based DUV Light-Emitting Materials. <i>Springer Series in Materials Science</i> , 2016 , 115-136	0.9	1
300	Investigation on photoluminescence properties and defect chemistry of GdAlO ₃ :Dy ³⁺ + Ba ²⁺ phosphors. <i>Optical Materials</i> , 2016 , 58, 524-530	3.3	3
299	Computational studies of positron states and annihilation parameters in semiconductors □ vacancy-type defects in group-III nitrides □ <i>Journal of Physics: Conference Series</i> , 2016 , 674, 012020	0.3	7
298	Electronic and optical characteristics of nm-plane GaN single crystal grown by hydride vapor phase epitaxy on a GaN seed synthesized by the ammonothermal method using an acidic mineralizer. <i>Japanese Journal of Applied Physics</i> , 2016 , 55, 05FA03	1.4	4
297	Enhanced photo/electroluminescence properties of Eu-doped GaN through optimization of the growth temperature and Eu related defect environment. <i>APL Materials</i> , 2016 , 4, 056103	5.7	21
296	Probing the effect of point defects on the leakage blocking capability of Al _{0.1} Ga _{0.9} N/Si structures using a monoenergetic positron beam. <i>Journal of Applied Physics</i> , 2016 , 120, 215702	2.5	14
295	2016 ,		11
294	Vacancy-type defects in Mg-doped GaN grown by ammonia-based molecular beam epitaxy probed using a monoenergetic positron beam. <i>Journal of Applied Physics</i> , 2016 , 119, 245702	2.5	8
293	Controlling the carrier lifetime of nearly threading-dislocation-free ZnO homoepitaxial films by 3d transition-metal doping. <i>Applied Physics Letters</i> , 2016 , 108, 021904	3.4	9
292	Vacancy behavior in Cu(In _{1-x} Ga _x)Se ₂ layers grown by a three-stage coevaporation process probed by monoenergetic positron beams. <i>Thin Solid Films</i> , 2016 , 603, 418-423	2.2	9
291	Vacancy defects and defect clusters in alkali metal ion-doped MgO nanocrystallites studied by positron annihilation and photoluminescence spectroscopy. <i>Applied Physics A: Materials Science and Processing</i> , 2016 , 122, 1	2.6	7
290	Vacancies in In _x Ga _{1-x} N/GaN multiple quantum wells fabricated on nm-plane GaN probed by a monoenergetic positron beam. <i>Applied Physics Express</i> , 2015 , 8, 051002	2.4	3
289	Low-resistivity m-plane freestanding GaN substrate with very low point-defect concentrations grown by hydride vapor phase epitaxy on a GaN seed crystal synthesized by the ammonothermal method. <i>Applied Physics Express</i> , 2015 , 8, 095501	2.4	19
288	Investigation on photoluminescence, electrical and positron lifetime of Eu ³⁺ activated Gd ₂ O ₃ phosphors. <i>Materials Chemistry and Physics</i> , 2015 , 166, 73-81	4.4	7
287	Molecular motion and relaxation below glass transition temperature in poly (methyl methacrylate) studied by positron annihilation. <i>Radiation Physics and Chemistry</i> , 2015 , 108, 81-86	2.5	12

286	Positron annihilation and cathodoluminescence study on inductively coupled plasma etched GaN. <i>Physica Status Solidi (B): Basic Research</i> , 2015 , 252, 913-916	1.3	3
285	Vacancy-type defects and their annealing behaviors in Mg-implanted GaN studied by a monoenergetic positron beam. <i>Physica Status Solidi (B): Basic Research</i> , 2015 , 252, 2794-2801	1.3	52
284	Recent Progress in Gas Barrier Thin Film Coatings on PET Bottles in Food and Beverage Applications. <i>Coatings</i> , 2015 , 5, 987-1001	2.9	34
283	. <i>IEEE Transactions on Semiconductor Manufacturing</i> , 2015 , 28, 92-95	2.6	4
282	Enhancement of the gas barrier property of polypropylene by introducing plasma-treated silane coating with SiO _x -modified top-surface. <i>Surface and Coatings Technology</i> , 2015 , 284, 377-383	4.4	9
281	Effect of incorporation of deuterium on vacancy-type defects of a-C:H films prepared by plasma CVD. <i>Applied Surface Science</i> , 2015 , 330, 142-147	6.7	3
280	Free Volume Profiles at Polymer/Solid Interfaces Probed by Focused Slow Positron Beam. <i>Macromolecules</i> , 2015 , 48, 1493-1498	5.5	8
279	Leaching properties of chromate-containing epoxy films using radiotracers, PALS and SEM. <i>Progress in Organic Coatings</i> , 2014 , 77, 257-267	4.8	29
278	Residual defects in low-dose arsenic-implanted silicon after high-temperature annealing. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2014 , 321, 54-58	1.2	5
277	Vacancy clusters introduced by CF ₄ -based plasma treatment in GaN probed with a monoenergetic positron beam. <i>Applied Physics Express</i> , 2014 , 7, 121001	2.4	5
276	Annealing behaviors of vacancy-type defects near interfaces between metal contacts and GaN probed using a monoenergetic positron beam. <i>Applied Physics Letters</i> , 2014 , 105, 052108	3.4	7
275	Investigation of defect related photoluminescence property of multicolour emitting Gd ₂ O ₃ :Dy ³⁺ + phosphor. <i>RSC Advances</i> , 2014 , 4, 34257	3.7	41
274	Characterization of polyethylene terephthalate films coated with thin Al _x Si _{1-x} O _y layers using monoenergetic positron beams. <i>Thin Solid Films</i> , 2014 , 552, 82-85	2.2	1
273	(Invited) Point Defect Characterization of Group-III Nitrides by Using Monoenergetic Positron Beams. <i>ECS Transactions</i> , 2014 , 61, 19-30	1	11
272	Impact of the difference in power frequency on diamond-like carbon thin film coating over 3-dimensional objects. <i>Thin Solid Films</i> , 2014 , 564, 45-50	2.2	5
271	Defects in nitride-based semiconductors probed by positron annihilation. <i>Journal of Physics: Conference Series</i> , 2014 , 505, 012009	0.3	1
270	First-principles calculation of positron states and annihilation parameters for group-III nitrides. <i>Journal of Physics: Conference Series</i> , 2014 , 505, 012010	0.3	26
269	Vacancy-type defects induced by grinding of Si wafers studied by monoenergetic positron beams. <i>Journal of Applied Physics</i> , 2014 , 116, 134501	2.5	10

268	Optically active vacancies in GaN grown on Si substrates probed using a monoenergetic positron beam. <i>Applied Physics Letters</i> , 2014 , 104, 082110	3.4	18
267	Impact of back-grinding-induced damage on Si wafer thinning for three-dimensional integration. <i>Japanese Journal of Applied Physics</i> , 2014 , 53, 05GE04	1.4	18
266	Formation of low resistance ohmic contacts in GaN-based high electron mobility transistors with BCl ₃ surface plasma treatment. <i>Applied Physics Letters</i> , 2013 , 103, 083508	3.4	27
265	Impact of Se flux on the defect formation in polycrystalline Cu(In,Ga)Se ₂ thin films grown by three stage evaporation process. <i>Journal of Applied Physics</i> , 2013 , 113, 064907	2.5	14
264	Excitonic emission dynamics in homoepitaxial AlN films studied using polarized and spatio-time-resolved cathodoluminescence measurements. <i>Applied Physics Letters</i> , 2013 , 103, 142103	3.4	21
263	Vacancy-type defects in In _x Ga _{1-x} N grown on GaN templates probed using monoenergetic positron beams. <i>Journal of Applied Physics</i> , 2013 , 114, 184504	2.5	11
262	Spatio-Time-Resolved Cathodoluminescence Studies on Freestanding GaN Substrates Grown by Hydride Vapor Phase Epitaxy. <i>ECS Transactions</i> , 2013 , 50, 1-8	1	2
261	Influence of wafer thinning process on backside damage in 3D integration 2013 ,		2
260	Vacancy-type defects introduced by plastic deformation of GaN studied using monoenergetic positron beams. <i>Journal of Applied Physics</i> , 2013 , 114, 084506	2.5	8
259	Development of a sample chamber with humidity control for an atmospheric positron probe microanalyzer. <i>Journal of Physics: Conference Series</i> , 2013 , 443, 012090	0.3	1
258	Vacancy reactions near the interface between electroplated Cu and barrier metal layers studied by monoenergetic positron beams. <i>Journal of Applied Physics</i> , 2013 , 114, 074510	2.5	3
257	Material design of plasma-enhanced chemical vapour deposition SiCH films for low- cap layers in the further scaling of ultra-large-scale integrated devices-Cu interconnects. <i>Science and Technology of Advanced Materials</i> , 2013 , 14, 055005	7.1	5
256	Characterization of Porous Structures in Advanced Low-kFilms with Thin TaN Layers Using Monoenergetic Positron Beams. <i>Japanese Journal of Applied Physics</i> , 2013 , 52, 106501	1.4	5
255	Point defects introduced by InN alloying into In _x Ga _{1-x} N probed using a monoenergetic positron beam. <i>Journal of Applied Physics</i> , 2013 , 113, 123502	2.5	7
254	Time-resolved luminescence studies on AlN and high AlN mole fraction AlGa _N alloys. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2013 , 10, 501-506		6
253	Impacts of Si-doping and resultant cation vacancy formation on the luminescence dynamics for the near-band-edge emission of Al _{0.6} Ga _{0.4} N films grown on AlN templates by metalorganic vapor phase epitaxy. <i>Journal of Applied Physics</i> , 2013 , 113, 213506	2.5	73
252	Positron Annihilation Spectroscopy on Nitride-Based Semiconductors. <i>Japanese Journal of Applied Physics</i> , 2013 , 52, 08JJ02	1.4	20
251	The Effects of Plasma Treatments and Subsequent Atomic Layer Deposition on the Pore Structure of a k = 2.0 Low-k Material. <i>ECS Journal of Solid State Science and Technology</i> , 2013 , 2, N103-N109	2	4

250	Positron annihilation lifetime spectroscopy of mechanically milled protein fibre powders and their free volume aspects. <i>Journal of Physics: Conference Series</i> , 2013 , 443, 012054	0.3	
249	Material characterization for advanced Si LSI process technology by means of positron annihilation. <i>Journal of Physics: Conference Series</i> , 2013 , 443, 012067	0.3	1
248	Chemical effect of Si ⁺ ions on the implantation-induced defects in ZnO studied by a slow positron beam. <i>Journal of Applied Physics</i> , 2013 , 113, 043506	2.5	4
247	Synthesis of silica nanoparticles using oil-in-water emulsion and the porosity analysis. <i>Journal of Sol-Gel Science and Technology</i> , 2012 , 64, 309-314	2.3	5
246	Using X-ray tomography, PALS and Raman spectroscopy for characterization of inhibitors in epoxy coatings. <i>Progress in Organic Coatings</i> , 2012 , 74, 726-733	4.8	15
245	Electromigration extendibility of Cu(Mn) alloy-seed interconnects, and understanding the fundamentals 2012 ,		9
244	Native cation vacancies in Si-doped AlGa _{1-x} N studied by monoenergetic positron beams. <i>Journal of Applied Physics</i> , 2012 , 111, 013512	2.5	45
243	Positron annihilation studies on the behaviour of vacancies in LaAlO ₃ /SrTiO ₃ heterostructures. <i>Journal Physics D: Applied Physics</i> , 2012 , 45, 445305	3	5
242	Vacancy-Type Defects Introduced by Gas Cluster Ion-Implantation on Si Studied by Monoenergetic Positron Beams. <i>Japanese Journal of Applied Physics</i> , 2012 , 51, 111801	1.4	2
241	Variation of Chemical Vapor Deposited SiO ₂ Density Due to Generation and Shrinkage of Open Space During Thermal Annealing. <i>Japanese Journal of Applied Physics</i> , 2012 , 51, 021101	1.4	3
240	Vacancy-type defects in In _x Ga _{1-x} N alloys probed using a monoenergetic positron beam. <i>Journal of Applied Physics</i> , 2012 , 112, 014507	2.5	20
239	Free volume change of elongated polyethylene films studied using a positron probe microanalyzer. <i>Applied Physics Letters</i> , 2012 , 101, 203108	3.4	8
238	Time-resolved photoluminescence, positron annihilation, and Al _{0.23} Ga _{0.77} N/GaN heterostructure growth studies on low defect density polar and nonpolar freestanding GaN substrates grown by hydride vapor phase epitaxy. <i>Journal of Applied Physics</i> , 2012 , 111, 103518	2.5	56
237	In-situ characterization of free-volume holes in polymer thin films under controlled humidity conditions with an atmospheric positron probe microanalyzer. <i>Applied Physics Letters</i> , 2012 , 101, 014102 ^{3,4}	3.4	21
236	Vacancy clustering and its dissociation process in electroless deposited copper films studied by monoenergetic positron beams. <i>Journal of Applied Physics</i> , 2012 , 111, 104506	2.5	10
235	Defect characterization in Mg-doped GaN studied using a monoenergetic positron beam. <i>Journal of Applied Physics</i> , 2012 , 111, 014508	2.5	28
234	Vacancy-Type Defects Introduced by Gas Cluster Ion-Implantation on Si Studied by Monoenergetic Positron Beams. <i>Japanese Journal of Applied Physics</i> , 2012 , 51, 111801	1.4	3
233	Variation of Chemical Vapor Deposited SiO ₂ Density Due to Generation and Shrinkage of Open Space During Thermal Annealing. <i>Japanese Journal of Applied Physics</i> , 2012 , 51, 021101	1.4	3

232	Impact of Cu/III ratio on the near-surface defects in polycrystalline CuGaSe ₂ thin films. <i>Applied Physics Letters</i> , 2011 , 98, 112105	3.4	16
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40	Positron Annihilation in Vitreous Silica Glasses. <i>Japanese Journal of Applied Physics</i> , 1993 , 32, 2687-2691	1.4	16
39	Characterization of Separation-by-Implanted-Oxygen Wafers with Monoenergetic Positron Beams. <i>Japanese Journal of Applied Physics</i> , 1993 , 32, 3682-3686	1.4	21
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